

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC643A

DESCRIPTION

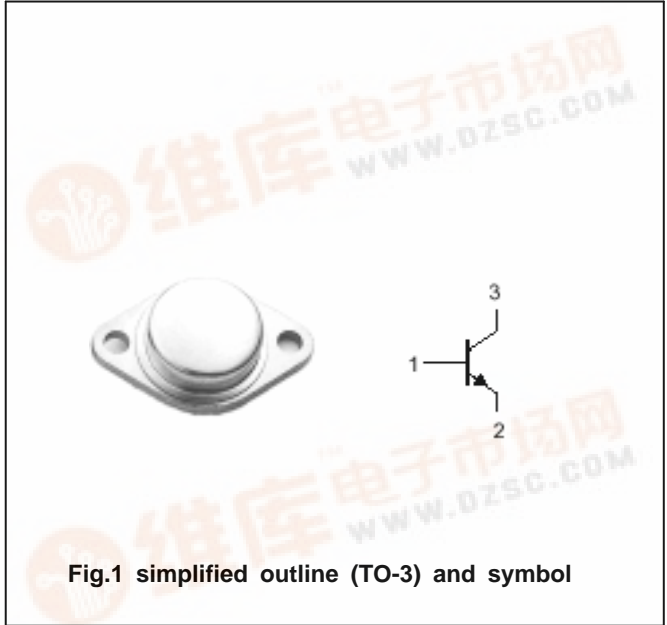
- With TO-3 package
- High voltage,high reliability
- Low collector saturation voltage

APPLICATIONS

- For color TV horizontal output applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	700	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _c	Collector current		2.5	A
P _c	Collector power dissipation	T _c =25	50	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =100mA; I _B =0	700			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2A; I _B =0.6A			8.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =2A; I _B =0.6A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =500V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			100	μA
h _{FE}	DC current gain	I _C =2A; V _{CE} =15V	5			
f _T	Transition frequency	I _C =0.1A; V _{CE} =10V		2		MHz

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PACKAGE OUTLINE

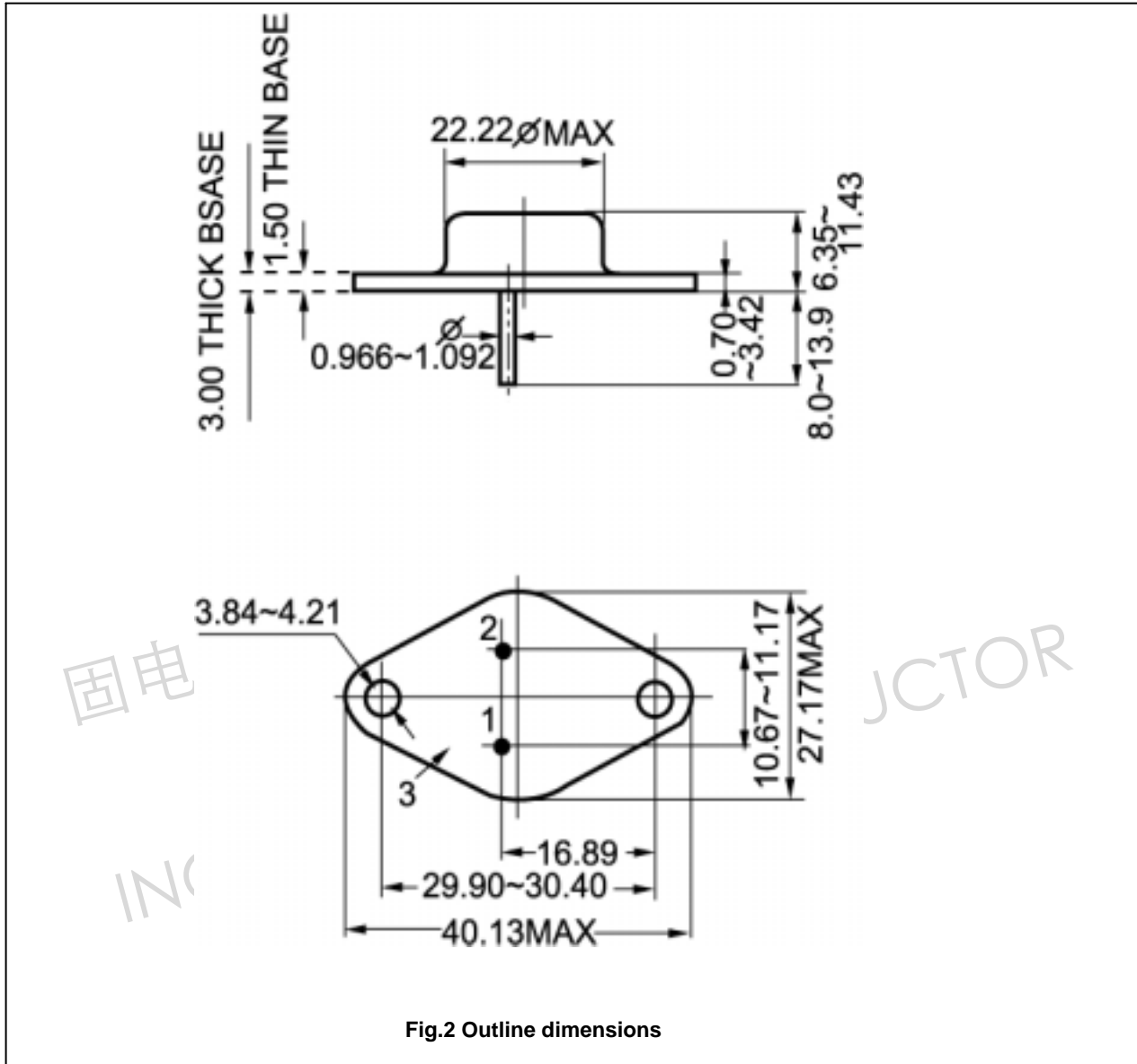


Fig.2 Outline dimensions